

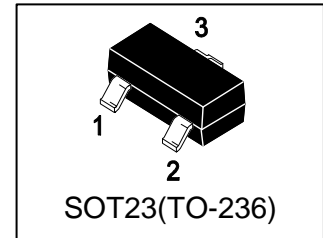
LBAW56LT1G

S-LBAW56LT1G

Monolithic Dual Switching Diode

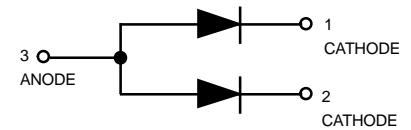
1. FEATURES

- We declare that the material of product compliance with RoHS requirements and Halogen Free.
- S- prefix for automotive and other applications requiring unique site and control change requirements; AEC-Q101 qualified and PPAP capable.



2. DEVICE MARKING AND ORDERING INFORMATION

| Device | Marking | Shipping |
|------------|---------|-----------------|
| LBAW56LT1G | A1 | 3000/Tape&Reel |
| LBAW56LT3G | A1 | 10000/Tape&Reel |



3. MAXIMUM RATINGS(Ta = 25°C)

| Parameter | Symbol | Limits | Unit |
|----------------------------|------------|--------|------|
| Reverse Voltage | VR | 70 | V |
| Forward Current | IF | 200 | mA |
| Peak Forward Surge Current | IFM(surge) | 500 | mA |

4. THERMAL CHARACTERISTICS

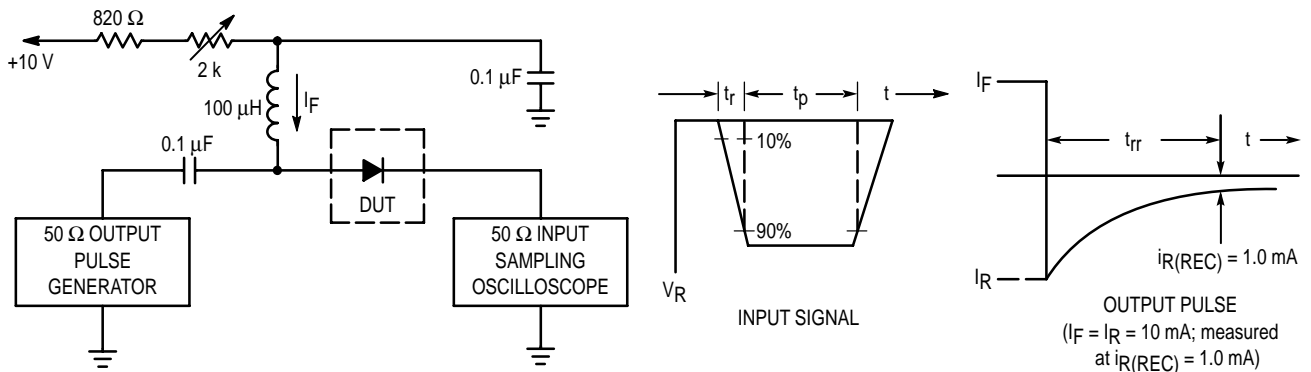
| Parameter | Symbol | Limits | Unit |
|--|----------|------------|-------------|
| Total Device Dissipation, FR-5 Board (Note 1) @ TA = 25°C Derate above 25°C | PD | 225 1.8 | mW mW/°C |
| Thermal Resistance, Junction-to-Ambient | RθJA | 556 | °C/W |
| Total Device Dissipation, Alumina Substrate (Note 2) @ TA = 25°C Derate above 25°C | PD | 300 2.4 | mW mW/°C |
| Thermal Resistance, Junction-to-Ambient | RθJA | 417 | °C/W |
| Junction and Storage Temperature | TJ, Tstg | -55 ~ +150 | °C |

1. FR-5 = 1.0 x 0.75 x 0.062 in.

2. Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

5. ELECTRICAL CHARACTERISTICS (Ta= 25°C)

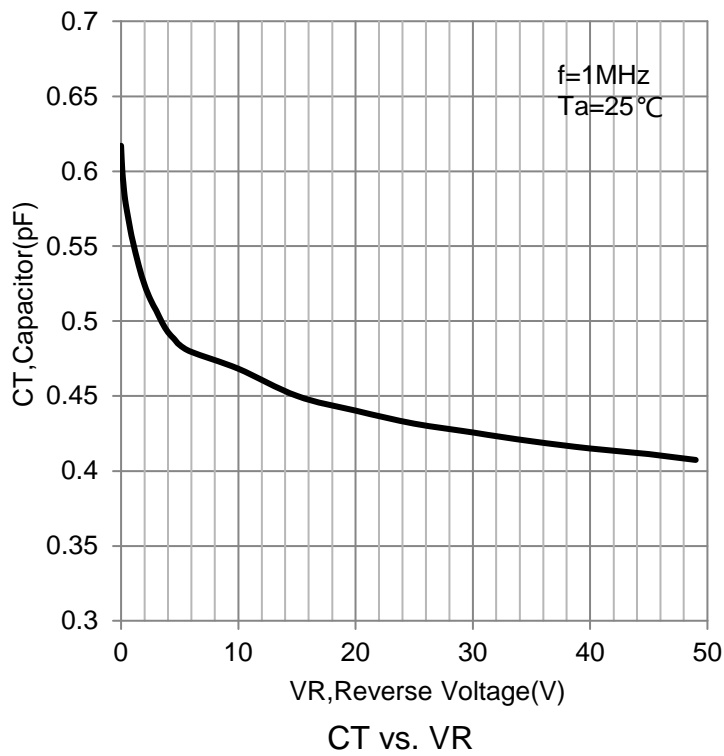
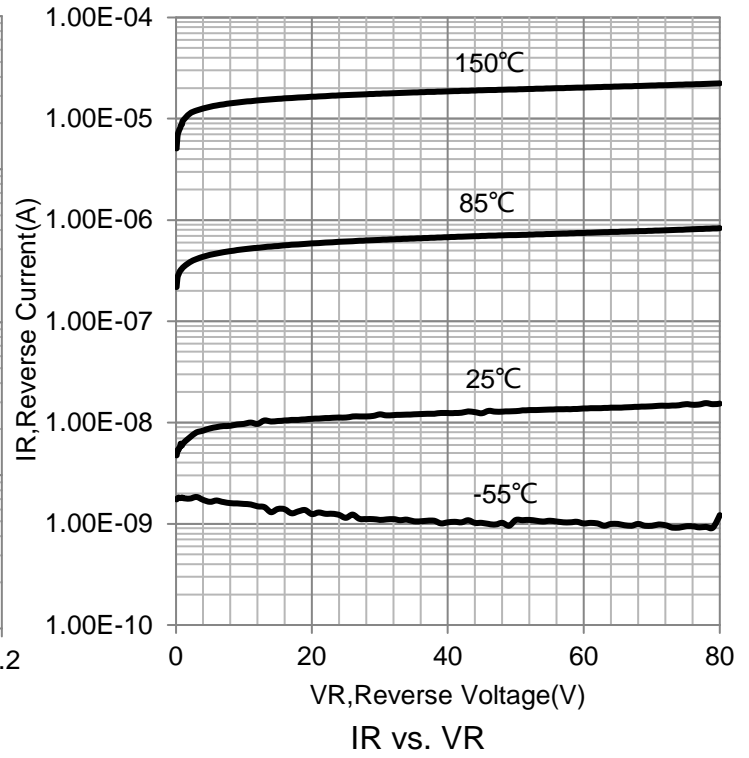
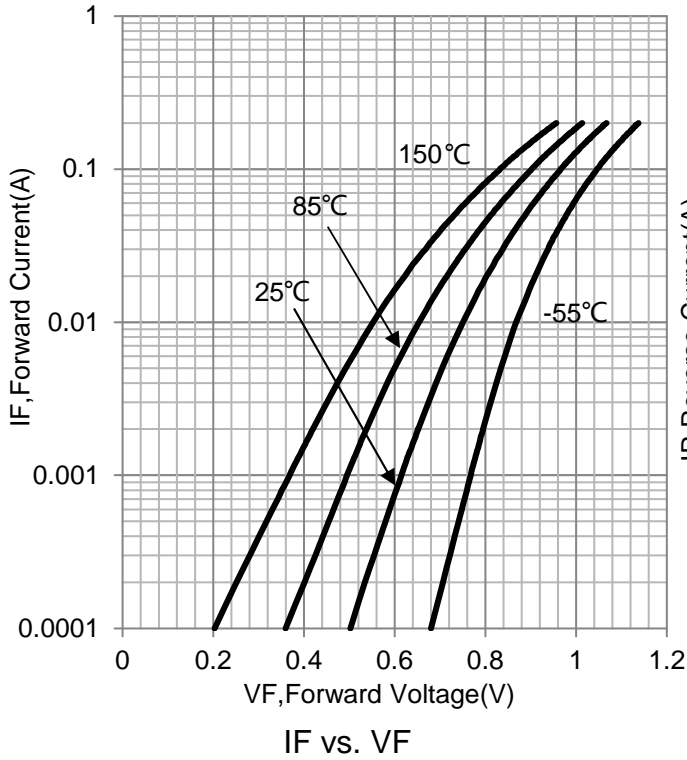
| Characteristic | Symbol | Min. | Typ. | Max. | Unit |
|---|--------|------|------|----------------------------|------|
| Reverse Breakdown Voltage (I(BR)=100μA) | VBR | 70 | - | - | V |
| Forward Voltage (IF = 1.0 mA) (IF = 10 mA) (IF = 50 mA) (IF = 150 mA) | VF | - | - | 715 855 1000 1250 | mV |
| Reverse Voltage Leakage Current (VR = 70V) (VR = 70V, TJ = 150°C) (VR = 25V, TJ = 150°C) | IR | - | - | 2.5 50 30 | μA |
| Diode Capacitance (VR = 0V, f = 1.0 MHz) | CD | - | - | 2.0 | pF |
| Reverse Recovery Time (IF=IR = 10 mA, IR(REC) = 1.0 mA, RL = 100 Ω) | trr | - | - | 6.0 | ns |



- Notes: 1. A 2.0 kΩ variable resistor adjusted for a Forward Current (IF) of 10 mA.
 2. Input pulse is adjusted so IR(peak) is equal to 10 mA.
 3. tp >> trr

Figure 1. Recovery Time Equivalent Test Circuit

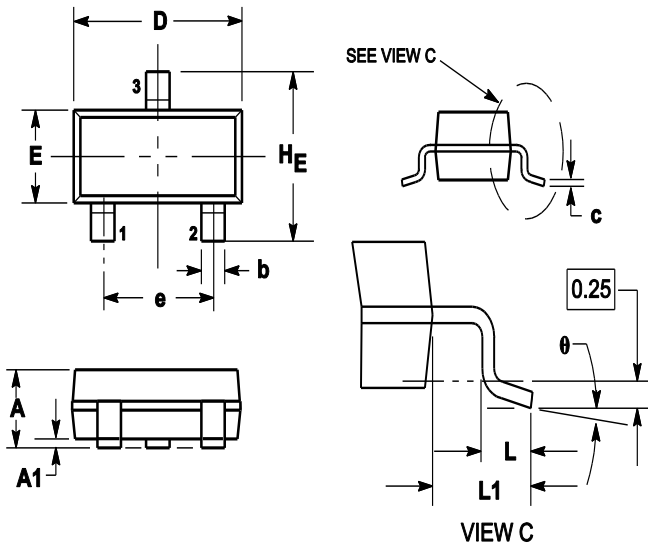
6.ELECTRICAL CHARACTERISTICS CURVES



7. OUTLINE AND DIMENSIONS

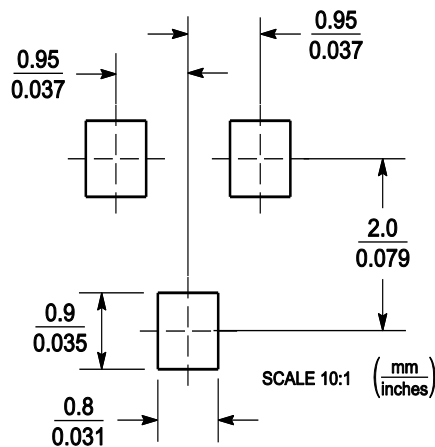
Notes:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.



| DIM | MILLIMETERS | | | INCHES | | |
|-------|-------------|------|------|--------|-------|-------|
| | MIN | NOM | MAX | MIN | NOM | MAX |
| A | 0.89 | 1 | 1.11 | 0.035 | 0.04 | 0.044 |
| A1 | 0.01 | 0.06 | 0.1 | 0.001 | 0.002 | 0.004 |
| b | 0.37 | 0.44 | 0.5 | 0.015 | 0.018 | 0.02 |
| c | 0.09 | 0.13 | 0.18 | 0.003 | 0.005 | 0.007 |
| D | 2.80 | 2.9 | 3.04 | 0.11 | 0.114 | 0.12 |
| E | 1.20 | 1.3 | 1.4 | 0.047 | 0.051 | 0.055 |
| e | 1.78 | 1.9 | 2.04 | 0.07 | 0.075 | 0.081 |
| L | 0.10 | 0.2 | 0.3 | 0.004 | 0.008 | 0.012 |
| L1 | 0.35 | 0.54 | 0.69 | 0.014 | 0.021 | 0.029 |
| HE | 2.10 | 2.4 | 2.64 | 0.083 | 0.094 | 0.104 |
| theta | 0° | --- | 10° | 0° | --- | 10° |

8. SOLDERING FOOTPRINT



单击下面可查看定价，库存，交付和生命周期等信息

[>>LRC\(乐山无线电\)](#)